# International Rectifier

# **6GBU Series**

## 6.0 Amps Single Phase Full Wave

### **Bridge Rectifier**

#### **Features**

- Diode chips are glass passivated
- Suitable for Universal hole mounting
- Easy to assemble & install on P.C.B.
- High Surge Current Capability
- High Isolation between terminals and molded case (1500 V<sub>RMS</sub>)
- Lead free terminals solderable as per MIL-STD-750 Method 2026
- Terminals suitable for high temperature soldering at 260°C for 8-10 secs
- UL E215862 approved

# $I_{O(AV)} = 6A$ $V_{RRM} = 50/800V$

#### Description

These GBU Series of Single Phase Bridges consist of four glass passivated silicon junction connected as a Full Wave Bridge. These four junctions are encapsulated by plastic molding technique. These Bridges are mainly used in Switch Mode power supply and in industrial and consumer equipment.

#### **Major Ratings and Characteristics**

Parameters		6GBU	Units	
Io		6	Α	
	@T <sub>C</sub>	100	°C	
I <sub>FSM</sub>	@50Hz	175	Α	
	@60Hz	182	Α	
I <sup>2</sup> t	@ 50Hz	154	A <sup>2</sup> s	
	@60Hz	138	A <sup>2</sup> s	
$V_{RRM}$	range	50 to 800	V	
$T_{J}$		- 55 to 150	°C	



6GBU

#### **6GBU Series**

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#### **ELECTRICAL SPECIFICATIONS**

Voltage Ratings

Type number	Voltage Code	$V_{RRM}$ , max repetitive peak rev. voltage $T_J = T_J max$ .	V <sub>RMS</sub> , max RMS voltage T <sub>J</sub> = T <sub>J</sub> max. V	I <sub>RRM</sub> max. @ rated V <sub>RRM</sub> Τ <sub>J</sub> = 25°C μΑ	I <sub>RRM</sub> max. @ rated V <sub>RRM</sub> T <sub>J</sub> = 150°C μΑ
6GBU	005	50	35	5	400
	01	100	70	5	400
	02	200	140	5	400
	04	400	280	5	400
	06	600	420	5	400
	08	800	560	5	400

#### **Forward Conduction**

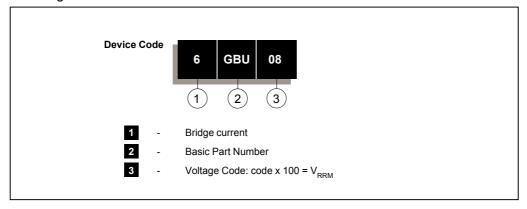
	Parameters	6GBU	Unit	Conditions	
Io	Maximum DC output current	6.0	Α	T <sub>C</sub> =100°C, Resi	stive & inductive load
		4.8		T <sub>C</sub> =100°C, Capa	acitive load
I <sub>ESM</sub>	Maximum peak, one-cycle	175		t = 10ms	
	non-repetitive surge current,				
	following any rated load condition	182		t = 8.3ms	T <sub>J</sub> =150°C
	and with rated V <sub>RRM</sub> reapplied				
I <sup>2</sup> t	Maximum I <sup>2</sup> t for fusing,	154	A <sup>2</sup> s	t = 10ms	
	initial T <sub>J</sub> =T <sub>J</sub> max	138		t = 8.3ms	
V <sub>FM</sub>	Maximum peak forward voltage	1.0	V	T <sub>J</sub> =25°C,I <sub>FM</sub> =6	A
	per diode				
I <sub>RM</sub>	Typical peak reverse leakage	5.0	μΑ	T <sub>J</sub> = 25°C, 1009	√V <sub>RRM</sub>
	current per diode	400	T <sub>J</sub> =150°C, 100%V <sub>RRM</sub>		√V <sub>RRM</sub>
$V_{RRM}$	Maximum repetitive peak	50 to 800	V		
	reverse voltage range				

#### **Thermal and Mechanical Specifications**

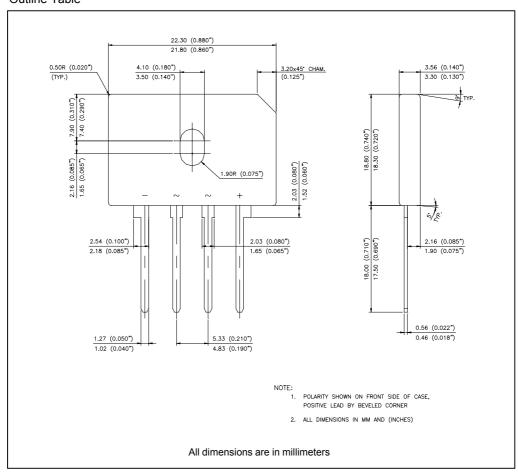
	Parameters	6GBU	Unit	Conditions
T	Operating and storage	-55 to 150	°C	
T <sub>stg</sub>	temperature range			
R <sub>thJC</sub>	Max. thermal resistance	2.2	°C/W	DC rated current through bridge (1)
	junction to case			
R <sub>thJA</sub>	Thermal resistance,	7.4	°C/W	DC rated current through bridge (1)
	junction to ambient			
W	Approximateweight	4(0.14)	g (oz)	
Т	MountingTorque	1.0	Nm	Bridge to Heatsink
		9.0	Lb.in	

Note (1): Bridge mounted on Aluminum heat sink of dim 65 x 35 x 1.5mm, use silicon thermal compound heat transfer and bolt down using 3mm screw

#### Ordering Information Table



#### **Outline Table**



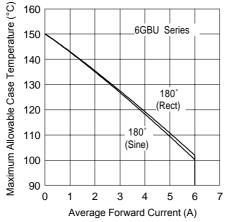


Fig. 1 - Current Ratings Characteristics

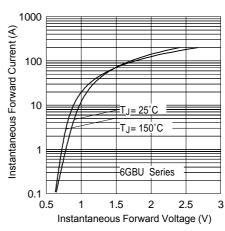


Fig. 2 - Forward Voltage Drop Characteristics

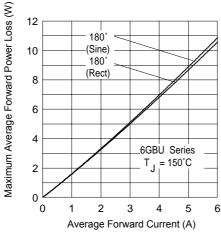
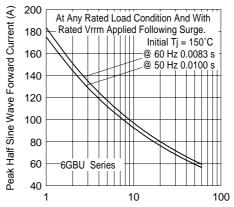


Fig. 3 - Total Power Loss Characteristics



Number of Equal Amplitude Half Cycle Current Pulses (N) Fig. 4 - Maximum Non-Repetitive Surge Current

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Data and specifications subject to change without notice. This product has been designed and qualified for Consumer Level.

Qualification Standards can be found on IR's Web site.



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